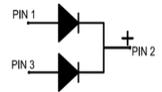
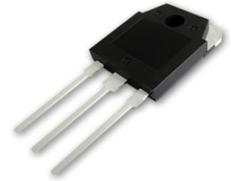


FEATURES

- Power pack
- Metal silicon junction ,majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss ,high efficiency
- High current capability ,low forward voltage drop
- High forward surge capability
- High frequency operation
- Meets MSL Level 1, per J-STD-020, LF MAX peak of
- Solder bath temperature 275°C maximum, 10s, per JESD22-B106
- Component in accordance to RoHS 2011/65/EU

TO-3P



MECHANICAL DATA

- Case: JEDEC TO-220F
- Molding compound meets UL94V-0 flammability rating
- Terminals: Lead solderable per J-STD-002 and JESD22-B102
- Polarity: As marked
- Mounting Torque: 10 in-lbs maximum

Dimensions in millimeters and (inches)

TYPICAL APPLICATIONS

For use in low voltage ,high frequency inverters ,DC/DC converters, free wheeling ,and polarity protection applications

MAXIMUM RATINGS

(Ratings at 25°C ambient temperature unless otherwise specified)

PRIMARY CHARACTERISTICS	
$I_F(AV)$	2×20A
V_{RRM}	200V
I_{FSM}	300A
V_f at $I_F=20.0A, Per leg$	0.85V
I_t	30 μ A
$T_J(MAX)$	150°C
Package	TO-3P
Diode variations	Common cathode

Parameter	Symbol	MBR40200CT	Unit
Maximum repetitive peak reverse voltage	V_{RRM}	200	V
Maximum average forward rectified current (see fig.1)	Per leg	20.0	A
	Total device	40.0	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method at rated T_L)	I_{FSM}	300	A
Peak repetitive reverse current per diode at $t_p=2 \mu s$ 1KHz	I_{RRM}	0.5	A
Operating junction and Storage temperature range	T_J, T_{stg}	-55 to+150	°C
Isolation voltage (TO-3P only) from terminals to heatsink $t=1 min$	V_{AC}	1500	V

RATINGS AND CHARACTERISTIC OF MBR40200CT

ELECTRICAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Parameter	Test Conditions		Symbol	TYP.	MAX.	Unit
Instantaneous forward voltage	Per leg I _F =20.0A	T _A =25°C	V _F ¹⁾	0.85	0.90	V
		T _A =100°C		0.78	–	
		T _A =125°C		0.75	–	
	Per leg I _F =15.0A	T _A =25°C		0.82	0.86	
		T _A =100°C		0.75	–	
		T _A =125°C		0.73	–	
Reverse current	V _R =100V	T _A =25°C	I _R ²⁾	30	60	μA
		T _A =100°C		3	5	mA
		T _A =125°C		12	20	
Typical junction capacitance	4V, 1MHz		C _J	570		pF

Notes: 1.Pulse test: 300 μs pulse width,1% duty cycle

2.Pulse test: pulse width≤40ms

THERMAL CHARACTERISTICS (T_A=25°C Unless otherwise noted)

Parameter	Symbol	MBR40200CT	Unit
Typical thermal resistance ³⁾	R _{θJC}	4.5	°C/W

3.Thermal resistance from junction to case

RATINGS AND CHARACTERISTIC OF MBR40100CT

FIG.1-FORWARD CURRENT DERATING CURVE

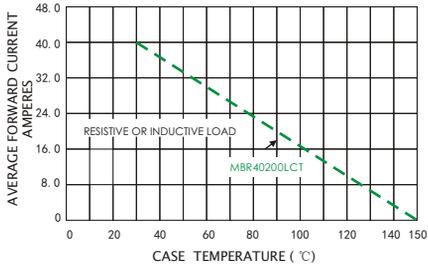


FIG.2-MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT

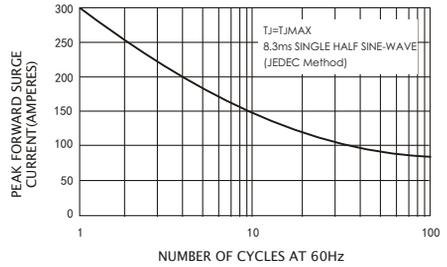


FIG.3-TYPICAL INSTANTANEOUS FORWARD CHARACTERISTICS

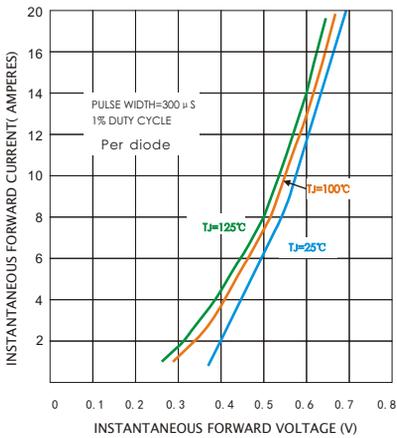


FIG.4-TYPICAL REVERSE CHARACTERISTICS

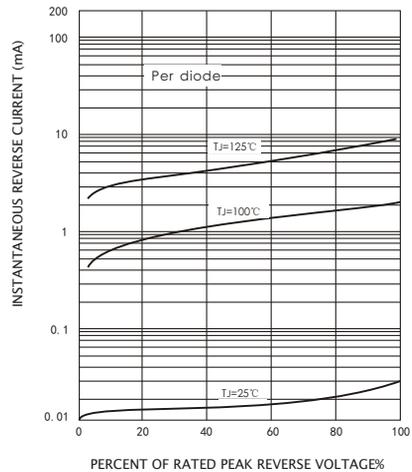
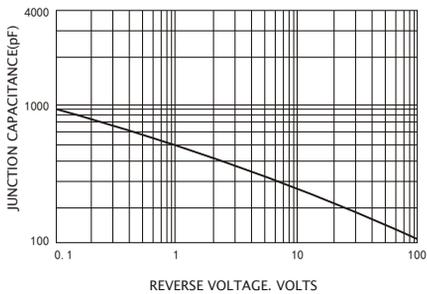


FIG.5-TYPICAL JUNCTION CAPACITANCE



PACKAGE OUTLINE DIMENSIONS

TO-3P

